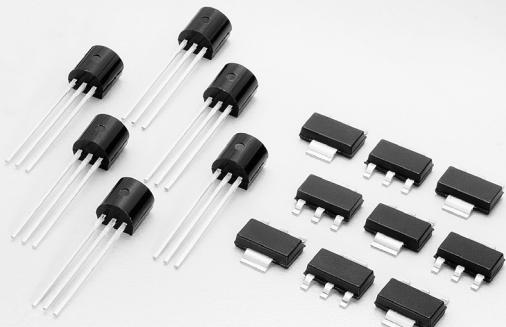


# S6002xS

### Description

The S6002xS offers high very high di/dt capability through small die planar construction design. It is glass-passivated to ensure long term reliability and parametric stability.

### Features

- Surge capability > 25Amps
- Blocking voltage ( $V_{DRM}/V_{RRM}$ ) capability — up to 600V
- High di/dt capability of 500A/ $\mu$ s
- Improved turn-off time ( $t_{q}$ ) < 55  $\mu$ sec.
- Sensitive gate for direct microprocessor interface
- Thru hole and surface mount packages
- RoHS compliant and Halogen-Free

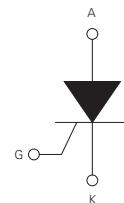
### Main Features

Symbol	Value	Unit
$I_{TRMS}$	2	A
$V_{DRM}/V_{RRM}$	600	V
$I_{GT}$	200	$\mu$ A

### Applications

The S6002xS is specifically designed for capacitor discharge application such as high-power gas flame ignition.

### Schematic Symbol



### Absolute Maximum Ratings

Symbol	Parameter		Value	Unit
$I_{TRMS}$	RMS on-state current (full sine wave)	TO-92	$T_c = 65^\circ C$	2
		SOT-223	$T_c = 95^\circ C$	
$I_{T(AV)}$	Average on-state current	TO-92	$T_c = 65^\circ C$	1.2
		SOT-223	$T_c = 95^\circ C$	
$I_{TSM}$	Non repetitive surge peak on-state current (Single cycle, $T_j$ initial = 25°C)	TO-92 SOT-223	$F = 50$ Hz	22.5
			$F = 60$ Hz	
$I^2t$	$I^2t$ Value for fusing	$t_p = 10$ ms	$F = 50$ Hz	2.5
$di/dt$	Critical rate of rise of on-state current $IG = 10$ mA	TO-92 SOT-223	$T_j = 25^\circ C$	500
$I_{GM}$	Peak gate current	$t_p = 20$ $\mu$ s	$T_j = 125^\circ C$	1.0
$P_{G(AV)}$	Average gate power dissipation		$T_j = 125^\circ C$	0.2
$T_{stg}$	Storage junction temperature range			-40 to 150
$T_j$	Operating junction temperature range			-40 to 125

### Electrical Characteristics ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)

Symbol	Description	Test Conditions	Value		Unit
			Min	Max	
$I_{GT}$	DC Gate Trigger Current	$V_D = 6\text{V}$ $R_L = 100\ \Omega$	20	200	$\mu\text{A}$
$V_{GT}$	DC Gate Trigger Voltage		—	0.8	V
$V_{GRM}$	Peak Reverse Gate Voltage	$I_{RG} = 10\mu\text{A}$	5	—	V
$I_H$	Holding Current	$R_{GK} = 1\ \text{k}\Omega$	—	5	mA
$V_{GD}$	Gate Non-Trigger Voltage	$V_D = V_{DRM}$ $R_{GK} = 1\ \text{k}\Omega$ $T_J = 125^\circ\text{C}$	0.2	-	V
dv/dt	Critical Rate-of-Rise of Off-State Voltage	$T_J = 125^\circ\text{C}$ $V_D = 67\% V_{DRM}$ Exponential Waveform $R_{GK} = 1\ \text{k}\Omega$	25	—	V/ $\mu\text{s}$
$t_q$	Turn-Off Time	$I_T = 0.5\text{A}$	—	55	$\mu\text{s}$
$t_{gt}$	Turn-On Time	$I_G = 10\text{mA}$ PW = 15 $\mu\text{sec}$ $I_T = 3.0\text{A}$ (pk)	—	3	$\mu\text{s}$

### Static Characteristics ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)

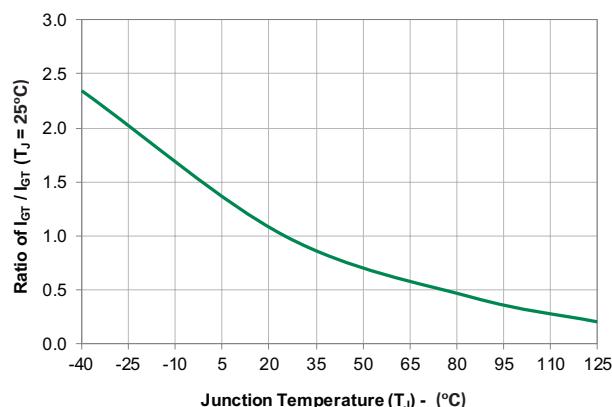
Symbol	Description	Test Conditions	Value		Unit
			Min	Max	
$V_{TM}$	Peak On-State Voltage	$I_{TM} = 3\text{A}$ (pk), $T_p = 380\mu\text{s}$	—	1.5	V
$I_{DRM} / I_{RRM}$	Off-State Current, Peak Repetitive	$T_J = 25^\circ\text{C} @ V_D = V_{DRM}$ $R_{GK} = 1\ \text{k}\Omega$	—	5	$\mu\text{A}$
		$T_J = 125^\circ\text{C} @ V_D = V_{DRM}$ $R_{GK} = 1\ \text{k}\Omega$	—	500	$\mu\text{A}$

### Thermal Resistances

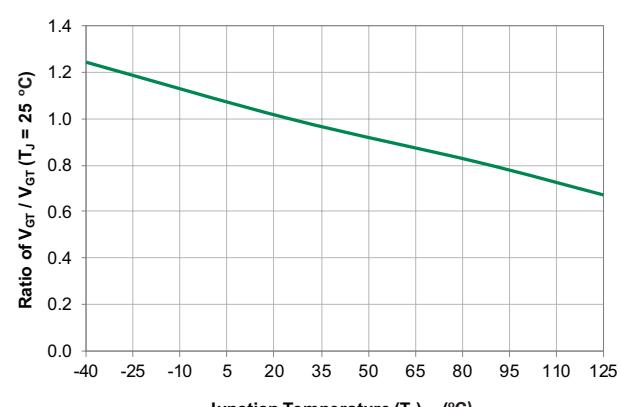
Symbol	Parameter			Value	Unit
$R_{\theta(JC)}$	Junction to case (AC)	$I_T = 1.5\text{A}$ <sup>1</sup> (RMS)	TO-92	30	$^\circ\text{C}/\text{W}$
			SOT-223	15	
$R_{\theta(J-A)}$	Junction to ambient	$I_T = 1.5\text{A}$ <sup>1</sup> (RMS)	TO-92	160	$^\circ\text{C}/\text{W}$
			SOT-223	60	

<sup>1</sup> 60Hz AC resistive load condition, 100% conduction.

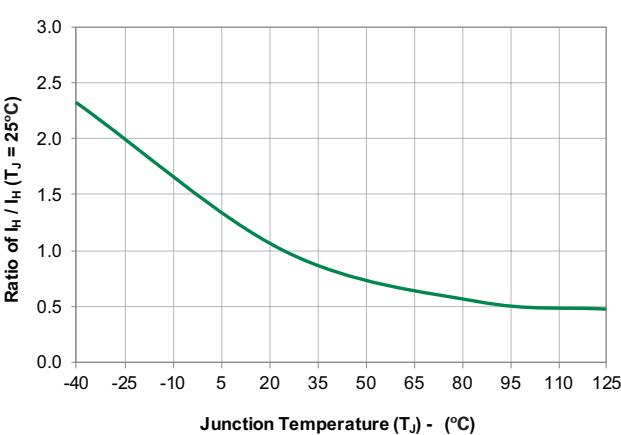
**Figure 1: Normalized DC Gate Trigger Current vs. Junction Temperature**



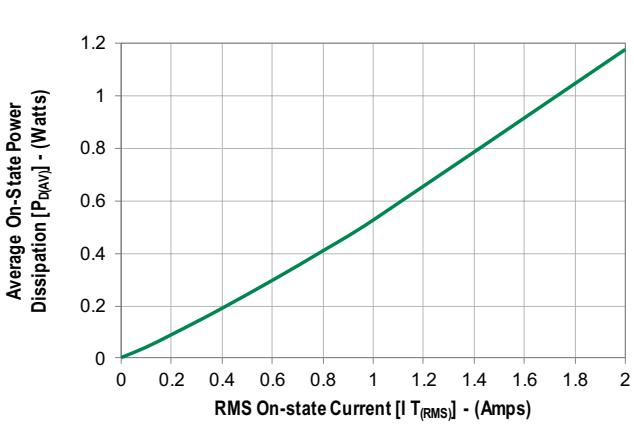
**Figure 2: Normalized DC Holding Current vs. Junction Temperature**



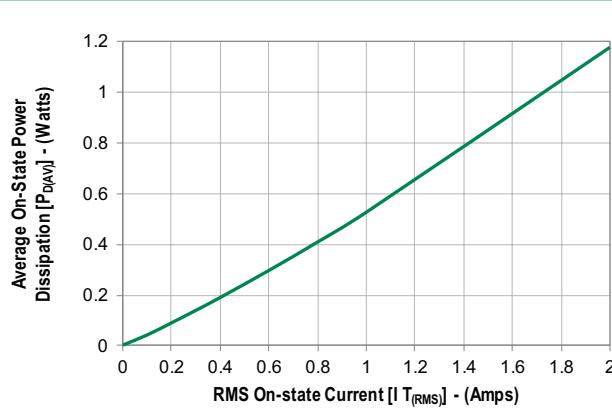
**Figure 3: Normalized DC Gate Trigger Voltage vs. Junction Temperature**



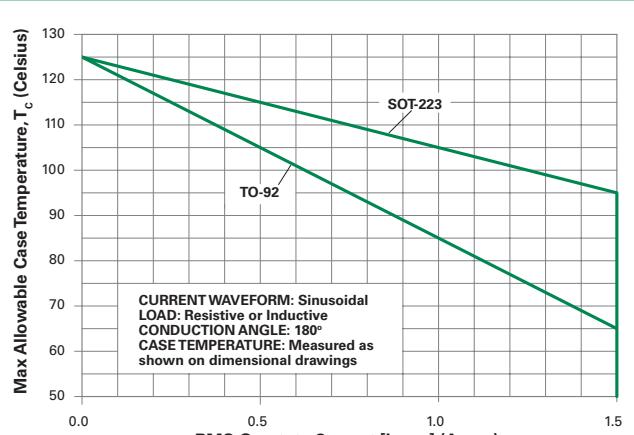
**Figure 4: On-State Current vs. On-State Voltage (Typical)**



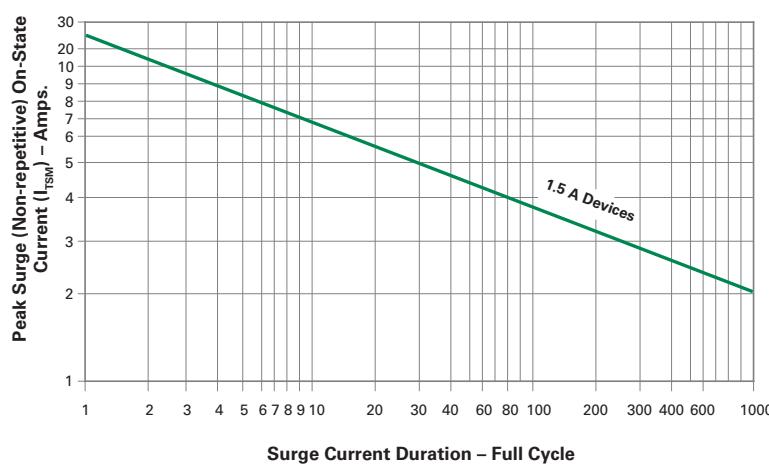
**Figure 5: Power Dissipation (Typical) vs. RMS On-State Current**



**Figure 6: Maximum Allowable Case Temperature vs. On-State Current**



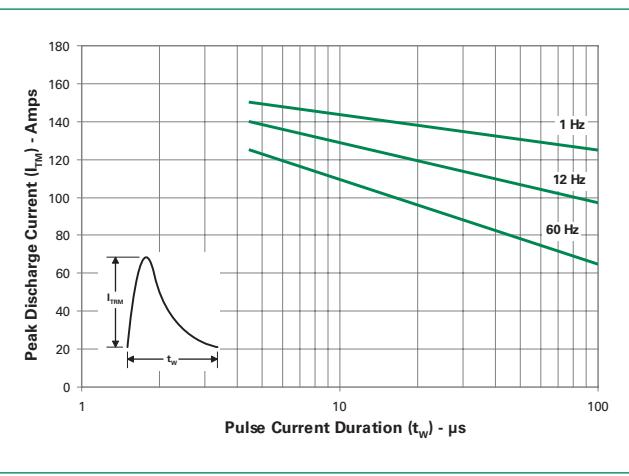
**Figure 7: Surge Peak On-State Current vs. Number of Cycles**



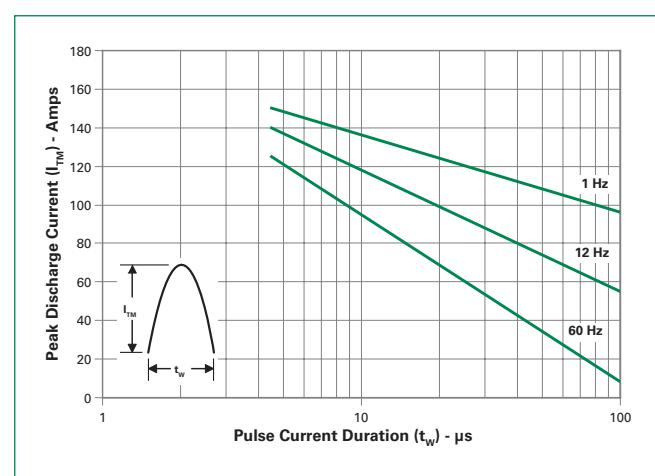
Supply Frequency: 60Hz Sinusoidal  
 Load: Resistive  
 RMS On-State Current ( $I_{TIRMS}$ ): Max Rated Value at Specific Case Temperature

- Notes:
1. Gate control may be lost during and immediately following surge current interval.
  2. Overload may not be repeated until junction temperature has returned to steady-state rated value.

**Figure 8: Peak Repetitive Capacitor Discharge Current**

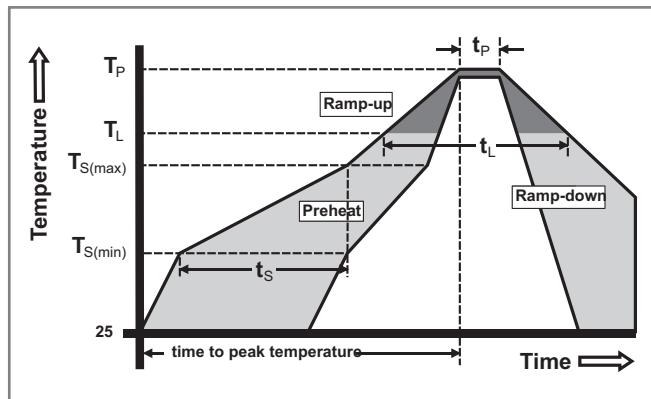


**Figure 9: Peak Repetitive Sinusoidal Pulse Current**



### Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	-Temperature Min ( $T_{s(min)}$ )	150°C
	-Temperature Max ( $T_{s(max)}$ )	200°C
	-Time (min to max) ( $t_s$ )	60 – 180 secs
Average ramp up rate (Liquidus Temp) ( $T_L$ ) to peak		5°C/second max
$T_{s(max)}$ to $T_L$ - Ramp-up Rate		5°C/second max
Reflow	-Temperature ( $T_L$ ) (Liquidus)	217°C
	-Time (min to max) ( $t_s$ )	60 – 150 seconds
Peak Temperature ( $T_p$ )		260 <sup>+0/-5</sup> °C
Time within 5°C of actual peak Temperature ( $t_p$ )		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature ( $T_p$ )		8 minutes Max.
Do not exceed		280°C



### Physical Specifications

<b>Terminal Finish</b>	100% Matte Tin-plated.
<b>Body Material</b>	UL Recognized compound meeting flammability rating V-0.
<b>Lead Material</b>	Copper Alloy

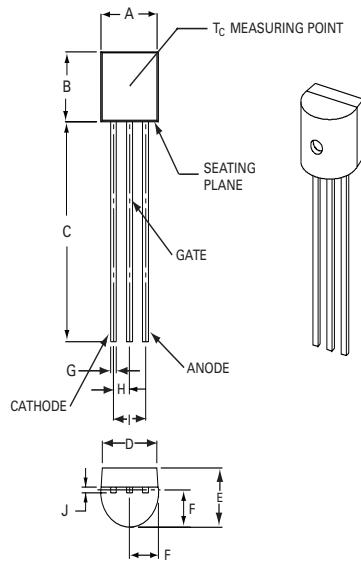
### Design Considerations

Careful selection of the correct component for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the component rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

### Environmental Specifications

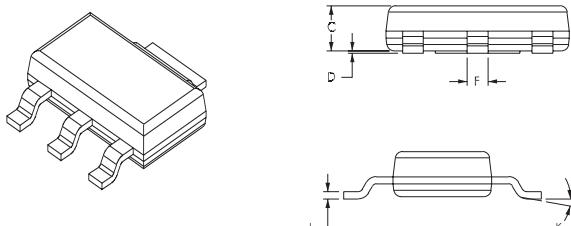
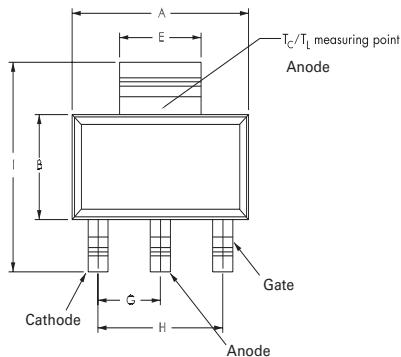
Test	Specifications and Conditions
<b>AC Blocking</b>	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 125°C for 1008 hours
<b>Temperature Cycling</b>	MIL-STD-750, M-1051, 1000 cycles; -55°C to +150°C; 15-min dwell-time
<b>Temperature/ Humidity</b>	EIA / JEDEC, JESD22-A101 1008 hours; 160V - DC: 85°C; 85% rel humidity
<b>High Temp Storage</b>	MIL-STD-750, M-1031, 1008 hours; 150°C
<b>Low-Temp Storage</b>	1008 hours; -40°C
<b>Resistance to Solder Heat</b>	MIL-STD-750 Method 2031
<b>Solderability</b>	ANSI/J-STD-002, category 3, Test A
<b>Lead Bend</b>	MIL-STD-750, M-2036 Cond E

### Dimensions – TO-92 (E Package)

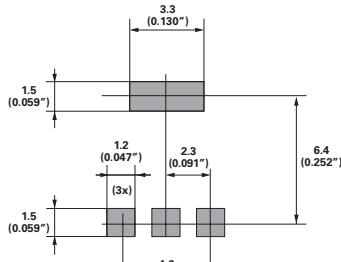


Dimensions	Inches		Millimeters	
	Min	Max	Min	Max
A	0.175	0.205	4.450	5.200
B	0.170	0.210	4.320	5.330
C	0.500	—	12.700	—
D	0.135	—	3.430	—
E	0.125	0.165	3.180	4.190
F	0.080	0.105	2.040	2.660
G	0.016	0.021	0.407	0.533
H	0.045	0.055	1.150	1.390
I	0.095	0.105	2.420	2.660
J	0.015	0.020	0.380	0.500

### Dimensions – SOT-223



Pad Layout for SOT-223



Dimensions in Millimeters (Inches)

Dimensions	Inches			Millimeters		
	Min	Typ	Max	Min	Typ	Max
A	0.248	0.256	0.264	6.30	6.50	6.70
B	0.130	0.138	0.146	3.30	3.50	3.70
C	—	—	0.071	—	—	1.80
D	0.001	—	0.004	0.02	—	0.10
E	0.114	0.118	0.124	2.90	3.00	3.15
F	0.024	0.027	0.034	0.60	0.70	0.85
G	—	0.090	—	—	2.30	—
H	—	0.181	—	—	4.60	—
I	0.264	0.276	0.287	6.70	7.00	7.30
J	0.009	0.010	0.014	0.24	0.26	0.35
K	10° MAX					

## Product Selector

Part Number	Voltage	Gate Sensitivity	Package
	600V		
S6002ES	X	200µA	TO92
S6002TS	X	200µA	SOT223

## Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
S6002ES	S6002ES	0.217g	Bulk	2500
SS6002ESAP	S6002ES	0.217g	Ammo Pack	2000
S6002ESRP	S6002ES	0.217g	Tape & Reel	2000
S6002TSRP	S6002TS	0.120g	Tape & Reel	1000

## Part Numbering System

**SCR SERIES**

**VOLTAGE**  
60: 600V

**CURRENT**  
02: 2A

**PACKING TYPE**

Blank: Bulk Pack

RP: Reel Pack (TO-92)

AP: Embossed Carrier Pack (SOT-223)

**SENSITIVITY**

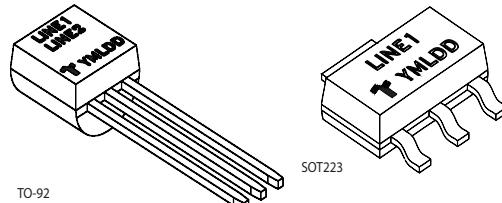
S: 200µA Sensitive SCR

**PACKAGE TYPE**

E: TO-92

T: SOT-223

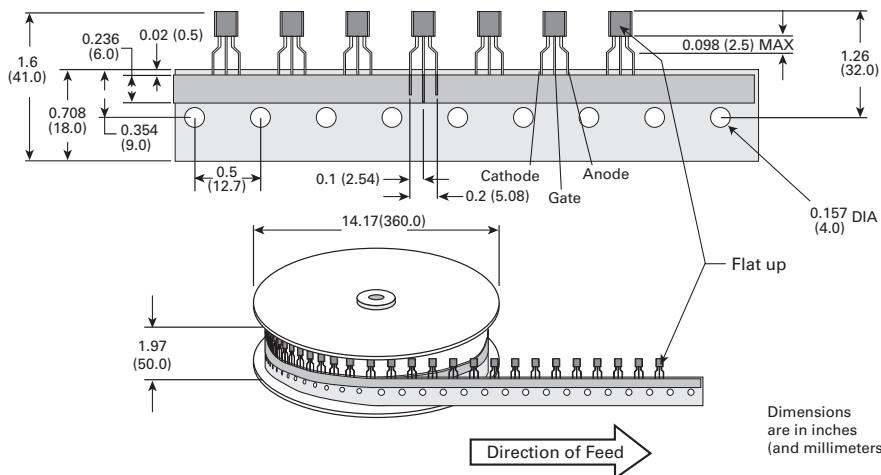
## Part Marking System



Line1 = Littelfuse Part Number  
Line2 = continuation...Littelfuse Part Number  
Y = Last Digit of Calendar Year  
M = Letter Month Code (A-L for Jan-Dec)  
L = Location Code  
DD = Calendar Date

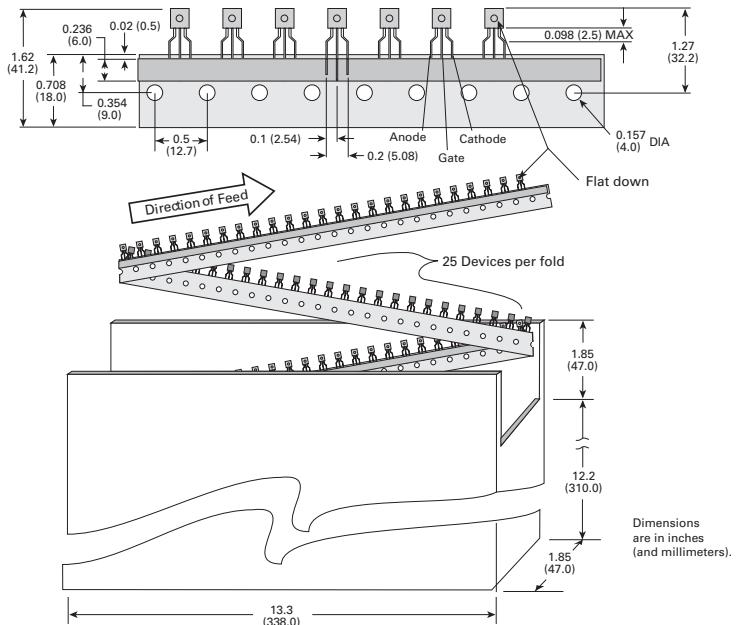
## TO-92 (3-lead) Reel Pack (RP) Radial Leaded Specifications

Meets all EIA-468-C Standards

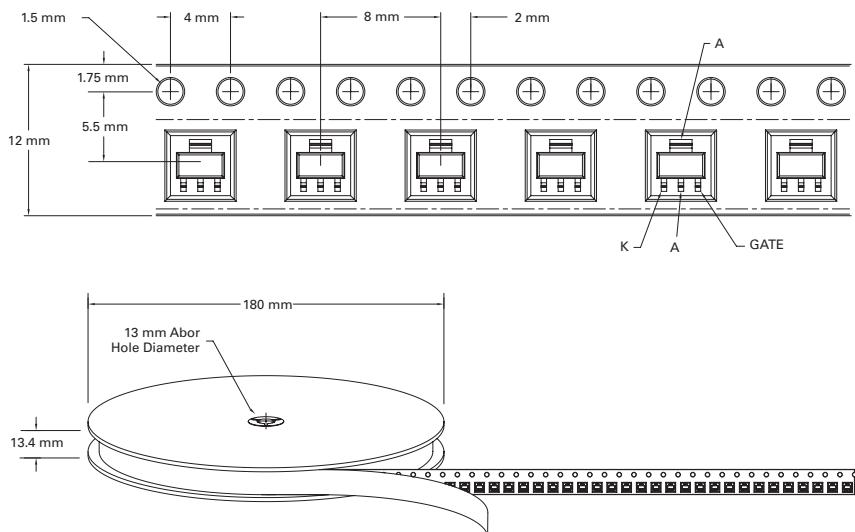


### TO-92 (3-lead) Ammo Pack (AP) Radial Leaded Specifications

Meets all EIA-468-C Standards



### SOT-223 Reel Pack (RP) Specifications



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